

# Perspectives on the merits of cubic silver antimony sulfide-selenide thin films for solar cells

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# Abstract

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- The silver antimony sulfide-selenide – cubic- $AgSb(S, Se)_2$  is a potential p-type semiconductor for application in thin-film solar cells. In this work, we present perspectives of  $AgSb(S, Se)_2$  to develop high-efficiency solar cells using this cubic metal chalcogenide semiconductor.
- Material characterization of the  $AgSbS_{1.3}Se_{0.7}$  solid solution confirms p-type conductivity with a bandgap of 1.48 eV and photoconductivity ( $\sigma$ ) of  $10^5 \Omega^{-1}cm^{-1}$ .
- The merit of incorporating silver atoms into the novel antimony chalcogenides ( $Sb_2S_3$ ,  $Sb_2Se_3$ ) comes from the transformation of orthorhombic structure into an FCC lattice, similar to that in rock salt structure.
- The absorption coefficient of  $\alpha > 10^5 cm^{-1}$  in the visible region of solar radiation in  $AgSbS_{1.3}Se_{0.7}$  allows a maximum photo-generated current density of  $29 mA/cm^2$  for a  $1 \mu m$  thick film under standard air-mass 1.5 global (1000 W/m<sup>2</sup>) solar radiation.
- The thin film solar cells of CdS/ $AgSbS_{1.3}Se_{0.7}$  heterojunction presents a fill factor of 0.64, open-circuit voltage of 537 mV, but a low short circuit current density of  $2 mA/cm^2$ .
- At this stage, chemical deposition has served for prototyping the solar cells. Improvements are expected using industrial chalcogenide growth techniques, which would enhance their carrier collection.
- $\sqrt{a + b^2}$
- $\sigma = 2 \times 10^{-8} \Omega^{-1}cm^{-1}$

# References

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